Preferred Device

**Schottky Barrier Diodes** 

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

### Features

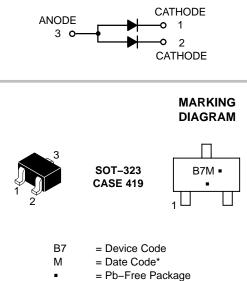
- Extremely Fast Switching Speed
- Low Forward Voltage 0.35 V (Typ) @  $I_F = 10 \text{ mAdc}$
- Pb–Free Packages are Available



## **ON Semiconductor®**

http://onsemi.com

# 30 VOLT SCHOTTKY BARRIER DETECTOR AND SWITCHING DIODES



(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

| Device     | Package              | Shipping <sup>†</sup> |
|------------|----------------------|-----------------------|
| BAT54AWT1  | SOT-323              | 3000/Tape & Reel      |
| BAT54AWT1G | SOT-323<br>(Pb-Free) | 3000/Tape & Reel      |
| BAT54AWT3  | SOT-323              | 10,000/Tape & Reel    |
| BAT54AWT3G | SOT-323<br>(Pb-Free) | 10,000/Tape & Reel    |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

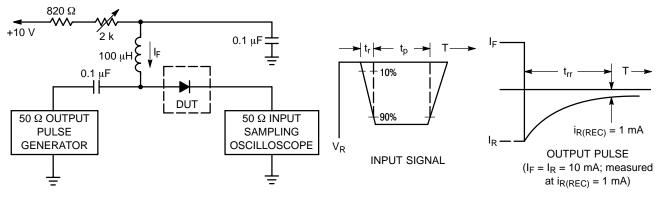
#### **MAXIMUM RATINGS** (T<sub>J</sub> = $125^{\circ}C$ unless otherwise noted)

| Rating  | Symbol           | Value       | Unit        |
|---|------------------|-------------|-------------|
| Reverse Voltage   | V <sub>R</sub>   | 30          | V           |
| Forward Power Dissipation<br>@ T <sub>A</sub> = 25°C<br>Derate above 25°C | P <sub>F</sub>   | 200<br>1.6  | mW<br>mW/°C |
| Forward Current (DC)  | ١ <sub>F</sub>   | 200 Max     | mA          |
| Junction Temperature  | TJ               | -55 to 125  | °C          |
| Storage Temperature Range   | T <sub>stg</sub> | -55 to +150 | °C          |
|   |                  |             |             |

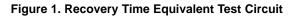
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

| Characteristic   | Symbol             | Min | Тур  | Max  | Unit |
|--|--------------------|-----|------|------|------|
| Reverse Breakdown Voltage $(I_R = 10 \ \mu A)$   | V <sub>(BR)R</sub> | 30  | -    | -    | V    |
| Total Capacitance $(V_R = 1.0 \text{ V}, \text{ f} = 1.0 \text{ MHz})$                         | CT                 | -   | 7.6  | 10   | pF   |
| Reverse Leakage<br>(V <sub>R</sub> = 25 V)   | ۱ <sub>R</sub>     | -   | 0.5  | 2.0  | μAdc |
| Forward Voltage<br>(I <sub>F</sub> = 0.1 mAdc)   | V <sub>F</sub>     | -   | 0.22 | 0.24 | Vdc  |
| Forward Voltage<br>(I <sub>F</sub> = 30 mAdc)  | V <sub>F</sub>     | -   | 0.41 | 0.5  | Vdc  |
| Forward Voltage<br>(I <sub>F</sub> = 100 mAdc)   | V <sub>F</sub>     | -   | 0.52 | 0.8  | Vdc  |
| Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, I_{R(REC)} = 1.0 \text{ mAdc}, Figure 1)$ | t <sub>rr</sub>    | -   | -    | 5.0  | ns   |
| Forward Voltage<br>(I <sub>F</sub> = 1.0 mAdc)   | V <sub>F</sub>     | -   | 0.29 | 0.32 | Vdc  |
| Forward Voltage<br>(I <sub>F</sub> = 10 mAdc)  | V <sub>F</sub>     | -   | 0.35 | 0.40 | Vdc  |
| Forward Current (DC)   | ١ <sub>F</sub>     | -   | -    | 200  | mAdc |
| Repetitive Peak Forward Current  | I <sub>FRM</sub>   | -   | -    | 300  | mAdc |
| Non–Repetitive Peak Forward Current<br>(t < 1.0 s)   | I <sub>FSM</sub>   | -   | -    | 600  | mAdc |

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (EACH DIODE)



Notes: 1. A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current (I<sub>F</sub>) of 10 mA. 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA. 3. t<sub>p</sub> » t<sub>rr</sub>



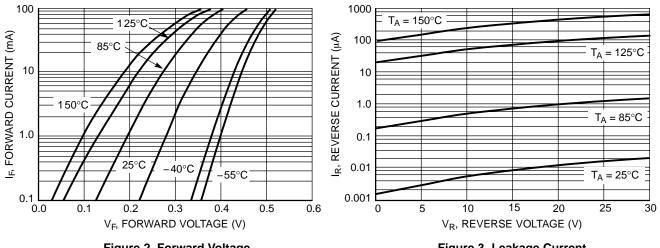


Figure 2. Forward Voltage

Figure 3. Leakage Current

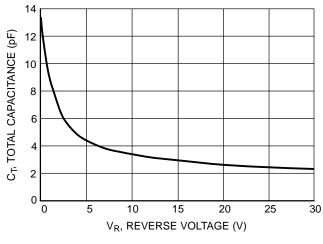
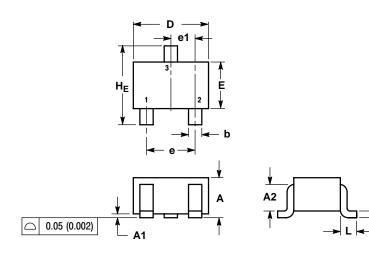


Figure 4. Total Capacitance

#### PACKAGE DIMENSIONS

SOT-323 (SC-70) CASE 419-04 ISSUE M

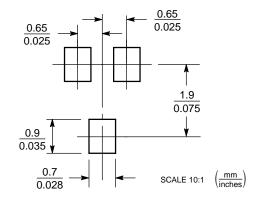


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.

CONTROLLING DIMENSION: INCH.

|     | MILLIMETERS |      |      | INCHES    |       |       |  |
|-----|-------------|------|------|-----------|-------|-------|--|
| DIM | MIN         | NOM  | MAX  | MIN       | NOM   | MAX   |  |
| Α   | 0.80        | 0.90 | 1.00 | 0.032     | 0.035 | 0.040 |  |
| A1  | 0.00        | 0.05 | 0.10 | 0.000     | 0.002 | 0.004 |  |
| A2  | 0.7 REF     |      |      | 0.028 REF |       |       |  |
| q   | 0.30        | 0.35 | 0.40 | 0.012     | 0.014 | 0.016 |  |
| С   | 0.10        | 0.18 | 0.25 | 0.004     | 0.007 | 0.010 |  |
| D   | 1.80        | 2.10 | 2.20 | 0.071     | 0.083 | 0.087 |  |
| Е   | 1.15        | 1.24 | 1.35 | 0.045     | 0.049 | 0.053 |  |
| e   | 1.20        | 1.30 | 1.40 | 0.047     | 0.051 | 0.055 |  |
| e1  | 0.65 BSC    |      |      | 0.026 BSC |       |       |  |
| Г   | 0.425 REF   |      |      | 0.017 REF |       |       |  |
| HE  | 2.00        | 2.10 | 2.40 | 0.079     | 0.083 | 0.095 |  |

**SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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